

Appl. No. 10/762,788
Reply to Examiner's Action dated January 22, 2004

IN THE CLAIMS:

Claims 1-22 (Canceled)

23. (Currently Amended) A process for fabricating an integrated circuit, comprising:
~~providing a doped substrate having a source, a drain and a channel extending from said source to said drain, wherein said source and said drain do not include a lightly doped regions;~~
~~forming an oxide over said channel a substrate, said oxide being defined by a width, said forming said oxide including~~

(a) exposing said substrate to a first oxidizing ambient, wherein exposing said substrate to a first oxidizing ambient includes increasing from an initial temperature to a first temperature below a threshold temperature at a first ramp rate, increasing from said first temperature to a second temperature below said threshold temperature at a second ramp rate, and growing at least a portion of said oxide;

(b) exposing said substrate to a second oxidizing ambient, wherein exposing said substrate to a second oxidizing ambient includes increasing from said second temperature to a third temperature at a third ramp rate, and increasing from said third temperature to a temperature above said threshold temperature at a fourth ramp rate; and

(c) cooling said substrate to a temperature below said threshold temperature,

wherein said oxide and said substrate form an interface that is substantially stress free and planar;

~~providing a doped substrate having forming within said substrate a source, a drain and a~~

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channel extending from said source to said drain, wherein said source and said drain do not include a lightly doped regions; and

forming a gate structure over a said substrate, said gate structure having a length of approximately 1.25 μ m or less and being coextensive with said width of said oxide.

24. (Previously Presented) A process as recited in claim 23, wherein said process further comprises forming said channel before forming said source and said drain.

Claim 25 (Canceled)

26. (Original) A process as recited in claim 24, wherein said channel is doped by a halo implantation.

27. (Original) A process as recited in claim 23, wherein said length is in the range of approximately 0.25 μ m to approximately 0.05 μ m.

28. (Previously Presented) A process as recited in claim 23, wherein said oxide layer has a first oxide portion and a second oxide portion.

29. (Original) A process as recited in claim 23, wherein a spacer is not formed adjacent said gate structure.

30. (Previously Presented) A process as recited in claim 23, wherein said oxide layer has a thickness in the range of approximately 1.5 nm to approximately 20.0 nm.

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31. (Previously Presented) A process as recited in claim 23, wherein said source and said drain have doping levels in the range of approximately $1 \times 10^{20}/\text{cm}^3$ to $5 \times 10^{20}/\text{cm}^3$.

32. (Previously Presented) A process as recited in claim 23, wherein said channel has a doping level in the range of approximately $1 \times 10^{16}/\text{cm}^3$ to approximately $1 \times 10^{19}/\text{cm}^3$.

Claims 33-40 (Canceled)

41. (New Claim) The process as recited in claim 23, wherein said first temperature below said threshold temperature is approximately 750°C - 850°C and said first ramp rate is approximately 50°C - 125°C per minute.

42. (New Claim) The process as recited in claim 23, wherein said second temperature below said threshold temperature is approximately 800°C - 900°C and said second ramp rate is approximately 10°C - 25°C per minute.

43. (New Claim) The process as recited in claim 23, wherein said substrate is oxidizable silicon and said threshold temperature is the viscoelastic temperature of SiO_2 .

44. (New Claim) The process as recited in claim 23, wherein step (b) further comprises: increasing from said second temperature to said third temperature at a ramp rate of approximately 5 - 15°C per minute in an ambient oxygen concentration of approximately 0% - 5% ; increasing from said third temperature to said temperature above said threshold temperature at a ramp rate of 5 - 10°C per minute in an ambient oxygen concentration of

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approximately 0%-5%; and

growing at least a portion of said oxide in an oxygen ambient concentration of about 25% or less.

45. (New Claim) The process as recited in claim 23, wherein step (c) further comprises: reducing from said temperature above said threshold temperature to approximately 800°C to 900°C at a rate of about 2°C-5°C per minute; and

reducing said temperature of approximately 800°C to 900°C to a boat pull temperature at a rate of about 35°C-65°C per minute, wherein said oxide portion formed in step (a) is a first oxide portion and acts as a stress sink to a second oxide portion formed in step (b) during at least a portion of said cooling.

46. (New Claim) The process as recited in claim 45, wherein said threshold temperature is the viscoelastic temperature of SiO₂.